

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
13 March 2008 (13.03.2008)

PCT

(10) International Publication Number
WO 2008/030188 A1

(51) International Patent Classification:
H01L 33/00 (2006.01) **H01L 23/482** (2006.01)

(74) Agent: CALLINAN, Keith, William; Lloyd Wisc, Tanjong Pagar, P.O. Box 636, Singapore 910816 (SG).

(21) International Application Number:
PCT/SG2007/000288

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(22) International Filing Date:
4 September 2007 (04.09.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
200606050-3 4 September 2006 (04.09.2006) SG

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(71) Applicant (for all designated States except US): TINGGI TECHNOLOGIES PRIVATE LIMITED [SG/SG]; 83 Science Park Drive, #03-01, Singapore 118258 (SG).

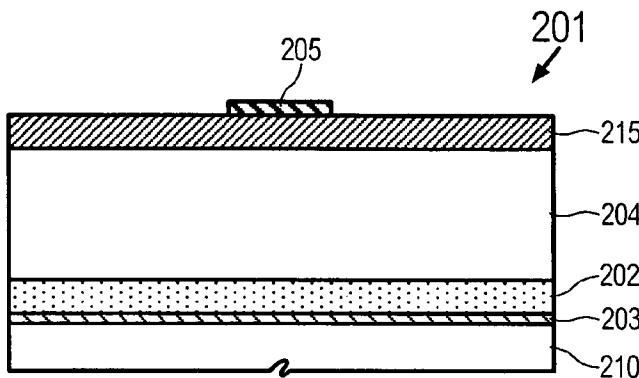
Declaration under Rule 4.17:
— of inventorship (Rule 4.17(iv))

(72) Inventors; and

(75) Inventors/Applicants (for US only): YUAN, Shu [AU/SG]; c/o Tinggi Technologies Private Limited, 83 Science Park Drive, #03-01, Singapore 118258 (SG). LIN, Shi Ming [CN/SG]; c/o Tinggi Technologies Private Limited, 83 Science Park Drive, #03-01, Singapore 118258 (SG).

Published:
— with international search report

(54) Title: ELECTRICAL CURRENT DISTRIBUTION IN LIGHT EMITTING DEVICES



(57) Abstract: A light emitting device is disclosed that has a plurality of epitaxial layers including an active layer; at least one of a reflective layer and an ohmic contact on a first side of the epitaxial layers; and a layer of a conductive metal on a second side of the epitaxial layers and having a light emitting surface. A terminal is on the light emitting surface, the terminal comprising an array for diffusing electrical current and minimizing its effect on light output. The array may have a bonding pad, an outer portion, and a joining portion connecting the bonding pad and the outer portion; the outer portion and the joining portion being for current dissipation.

Electrical Current Distribution in Light Emitting Devices

Field of the Invention

- 5 This invention relates to electrical current distribution in light emitting devices and refers particularly, through not exclusively, to apparatus for spreading the electrical current so as to maximize light output.

Reference to Related Application

10

Reference is made to our earlier Singapore patent application 20506301-1 filed 29 September 2005, the contents of which are incorporated herein by reference as if disclosed herein in their entirely.

15

Background of the Invention

In most light emitting devices such as for example, light emitting diodes and laser diodes, bonding pads occupy about 15% of the surface area of the light emitting surface. Where the bonding pad is located, light cannot be emitted.

20

Also, as the electrical current flows from the bonding pad to the active region and will follow the path of least resistance (normally the shortest path, in uniform materials) the maximum current flow, and thus maximum light output, is beneath the bonding pad. This results in a significant reduction in the light output.

25

Summary of the Invention

In accordance with a first preferred aspect there is provided a light emitting device comprising a plurality of epitaxial layers including an active layer; at least one of a reflective layer and an ohmic contact on a first side of the epitaxial layers; and a layer of 30 a conductive metal on a second side of the epitaxial layers and having a light emitting

surface. A terminal is on the light emitting surface. The terminal has an array for diffusing electrical current and minimizing its effect on light output.

The array may comprise a bonding pad, an outer portion, and a joining portion
5 connecting the bonding pad and the outer portion; the outer portion and the joining portion being for current dissipation. The outer portion may be at or adjacent a periphery of the light emitting surface. The joining portion may comprise a plurality of spokes joining the bonding pad and the outer portion.

10 There may be a second reflective layer between the array and the light emitting surface. Alternatively, the second reflective layer may be at a bottom of a trench in the light emitting surface.

In accordance with a second preferred aspect there is provided a method of fabricating a
15 light emitting device. The light emitting device has a plurality of epitaxial layers including an active layer, a reflective layer on a first side of the epitaxial layers, and a conductive metal on a second side of the epitaxial layers. The method includes forming a terminal on a light emitting surface of the conductive metal, the terminal having an array for diffusing electrical current and minimizing its effect on light output.

20 The forming of the array may be by forming a bonding pad, an outer portion, and a joining portion electrically connecting the bonding pad and the outer portion; the outer portion and the joining portion being for current dissipation. The outer portion may be at or adjacent a periphery of the light emitting surface. The joining portion may comprise a plurality of spokes joining the bonding pad and the outer portion.

25 The method may further comprise forming second reflective layer on the light emitting surface before forming the array on the second reflective layer.

30 Alternatively, the method may further comprise forming trench in the light emitting surface, forming a second reflective layer at a bottom of the trench, the array being formed on the second reflective layer.

Brief Description of the Drawings

In order that the present invention may be fully understood and readily put into practical effect, there shall now be described by way of non-limitative example only preferred 5 embodiments of the present invention, the description being with reference to the accompanying illustrative drawings.

In the drawings:

- 10 Figure 1 is a schematic side view of a light emitting device;
Figure 2 is a schematic side view of a preferred embodiment of a light emitting device;
Figure 3 is a stop pan view of the device of Figure 2;
Figure 4 is a vertical cross-section along the lines and in the direction of arrows 4-4 on Figure 3; and
15 Figure 5 is an enlarged view of the trench of Figure 4;
Figure 6 is an alternative to the arrangement of Figure 5;
Figure 7 to 13 are series of views corresponding to Figure 4 showing the fabrication of the device of Figures 2 to 4.

20 **Detailed Description of the Preferred Embodiments**

To first refer to Figure 1 there is shown a light emitting device 101 such as, for example, a light emitting diode or a laser diode, and having a reflective layer and/or ohmic contact 103 on a first side of a plurality of epitaxial layers including an active 25 region 102. A conductive metal layer 104 is on a second side of the epitaxial layers. The reflective layer 103 may be on the epitaxial layers and the ohmic contact on the reflective layer, or vice versa. There may be only one of them. A bonding pad 105 is provided on the light output surface 107. The electrical current flows in the metal layer 104 to the active layer 102 by the paths as shown with the dotted lines on Figure 1. As 30 can be seen, the maximum electrical current is concentrated under the bond pad 105. That means the maximum light emitted by the active layer 102 (as shown by the sold

lines) will also be concentrated under the bonding pad 105. Such light will be reflected back into layer 104 by the bonding pad 105. This significantly reduces the light output.

Figure 2 to 4 show a preferred embodiment where like reference numerals are used for
5 like components but the prefix number “1” is changed to “2”. Here, the bonding pad
105 is replaced by a terminal layer 215.

The terminal layer 215 comprises an array 214 of electrically conductive material,
preferably the same material as the bonding pad 205, and which is electrically
10 connected to both the bonding pad 205 and the light output surface 207. The array 214
is distributed over the surface 207 so that electrical current will flow from the terminal
layer 215 to the active region 202 in a diffused or distributed manner.

The array 214 preferably has the bonding pad 205 as its center so the distribution of the
array 214 is relatively uniform over the surface 207. Also, it is preferred for the array
214 to be of reduced height when compared with the bonding pad 205.

As shown, the array 214 comprises an outer portion 206 that is at or adjacent the
periphery of surface 207. This is to provide for light emission from at, and adjacent to,
20 the periphery of active region 202. Electrically and physically connecting the outer
portion 206 and the bonding pad 205 is a joining portion 208 that is, in this case, four
equally-spaced radial “spokes” extending from the bonding pad 205 to the outer portion
206. All spokes 208 are preferably identical, and are more preferably of the same
height and width as the outer portion 206. Although four spokes 208 are shown in a
25 cruciform shape, there may be any suitable number of spokes such as, for example, one,
two, three, four, five, six, and so forth.

Between the spokes 208 and the outer portion 206 are light-emitting openings 209 for
emission of light from light output surface 207.

The outer portion 206 and/or each spoke 208 or array 214 may be located in a trench
211 formed in the light output surface 207. The trench 211 may have a reflective layer

212 at its bottom 213 so that light propagated by active region 202 under the array 214 will be more efficiently reflected by reflective layer 212. The reflective layer 212 may have a diffusing surface so that light will be reflected from it at an angle other than perpendicular. The reflective layer 212 is electrically conductive to enable electric current to pass from array 214 to the active region 202. The reflecting layer 212 is preferably of the same shape and dimensions on surface 207 as the array 214.

As shown in Figure 6, the trench 211 may not be used and the reflective layer 212 may be applied directly to the light output surface 207 beneath array 214.

10

Figure 7 to 13 show the process. These are Figures 11 to 17 of the related application, and are the process step after the original sapphire substrate 4 is removed.

15

As shown in Figure 8, after removal of the sapphire substrate 4, the devices are isolated from each other by trench etching from the newly exposed surface 13 along the edges of the mesa, as shown in Figure 8 to 10, with a photoresist layer 6(d) protecting the regions of the n-type GaN layer 3 during the etching process.

20

Alternatively, the lowermost surface 13 of the n-type layer 3 may be cleaved at locations in alignment with the photoresists 12 and the dies separated. This is of advantage for laser diodes as the exposed side surfaces of the n-type layer 3 are substantially parallel, thus causing a large amount of total internal reflection. This acts as a light amplification system for improved, and directed light, output.

25

Pad etching takes place after applying a fifth resist layer 6(e) over the exposed surfaces of SiO₂ layer 8, the sides of the n-type GaN layer 3, and the center of the n-type GaN layer 3 [Figure 9(a) and (b)] thus forming projecting portions 14 and recess portions 15 of n-type GaN layer 3.

30

The resist 6(e) is removed and a further resist 6(f) applied over the exposed surfaces of the n-type GaN layer 3 and the outer periphery of the SiO₂ layer 8 to thus leave a gap 16 for die isolation. Etching takes place (Figure 10) through the gap 16 and the SiO₂

layer 8, and seed layer 11 until the ends of the thick photoresists 12 are exposed. The resist 6(f) is removed.

A final resist layer 6(g) is applied over all exposed lower-surfaces from the edge of the
5 SiO₂ layer 8 through to adjacent the center of the n-type GaN layer 3, where a central gap 17 remains (Figure 11).

An array 214 of layer or layers 18 of n-type metals are then applied over the resist 6(g)
with the layer 18 at the gap 17 at the center of the n-type GaN layer 3 being applied
10 directly to the GaN layer 3 (Figure 12). The resist layer 6(g) with the layer 18 attached,
is removed leaving the layer 18 attached to the center 17 of the n-type GaN layer 3
where gap 17 was previously located.

In this way the seed layers 11, 10, 9 and the copper layer 9(a) act as reflectors to
15 increase light output, with copper layer 9(a) being one terminal, thus not interfering
with light output. The second terminal is layer 18 in array 214 on the n-type layer 3 of
GaN and this is an array at and/or around the center of that layer 3, thus minimizing its
effect on light output, and increasing the diffusion of current.

20 Whilst there has been described in the foregoing description preferred embodiments of
the present invention, it will be understood by those skilled in the technology concerned
that many variations or modifications in details of design or construction may be made
without departing from the present invention.

THE CLAIMS

1. A light emitting device comprising:
 - (a) a plurality of epitaxial layers including an active layer;
 - (b) at least one of a reflective layer and an ohmic contact on a first side of the epitaxial layers;
 - (c) a layer of a conductive metal on a second side of the epitaxial layers and having a light emitting surface; and
 - (d) a terminal on the light emitting surface, the terminal comprising an array for diffusing electrical current and minimizing its effect on light output.
- 10
2. A light emitting devices as claimed in claim 1, wherein the array comprises a bonding pad, an outer portion, and a joining portion connecting the bonding pad and the outer portion; the outer portion and the joining portion being for current dissipation.
- 15
3. A light emitting device as claimed in claim 2, wherein the outer portion is at or adjacent a periphery of the light emitting surface.
- 20
4. A light emitting device as claimed in claim 2 or claim 3, wherein the joining portion comprises a plurality of spokes joining the bonding pad and the outer portion.
5. A light emitting device as claimed in any one of claims 1 to 4, wherein there is a second reflective layer between the array and the light emitting surface.
- 25
6. A light emitting device as claimed in any one of claims 2 to 4, wherein the second reflective layer is at a bottom of a trench in the light emitting surface.
7. A method of fabricating a light emitting device comprising a plurality of epitaxial layers including an active layer, a reflective layer on a first side of the epitaxial layers and a conductive metal on a second side of the epitaxial layer, the conductive metal having a light emitting surface; the method comprising:
30

on the light emitting surface of the conductive metal, forming a terminal comprising an array for diffusing electrical current and minimizing its effect on light output.

5 8. A method as claimed in claim 7, wherein the forming of the array is by forming a bonding pad, an outer portion, and a joining portion electrically connecting the bonding pad and the outer portion; the outer portion and the joining portion being for current dissipation.

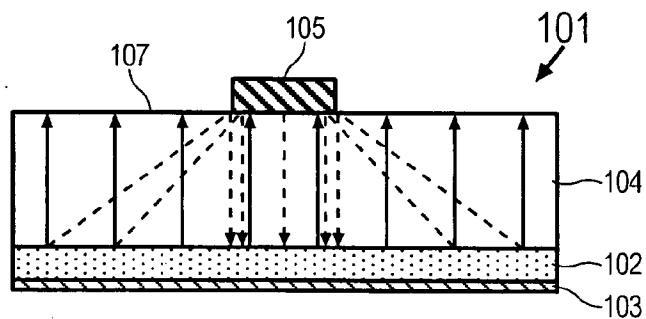
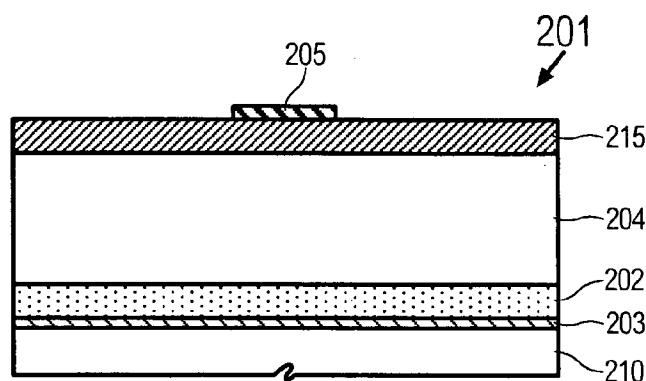
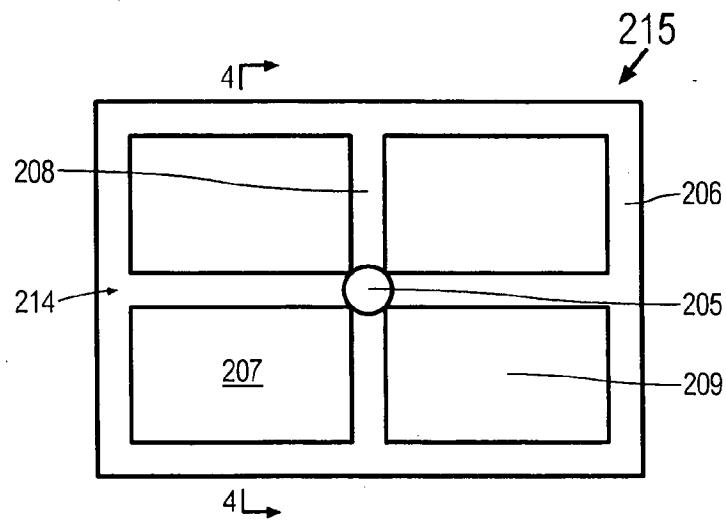
10 9. A method as claimed in claim 8, wherein the outer portion is at or adjacent a periphery of the light emitting surface.

10. A method as claimed in claim 8 or claim 9, wherein the joining portion comprises a plurality of spokes joining the bonding pad and the outer portion.

15 11. A method as claimed in any one of claims 7 to 10 further comprising forming a second reflective layer on the light emitting surface before forming the array on the second reflective layer.

20 12. A method as claimed in any one of claims 8 to 10 further comprising forming a trench in the light emitting surface, forming a second reflective layer at a bottom of the trench, the array being formed on the second reflective layer.

1/8

**FIGURE 1****FIGURE 2****FIGURE 3**

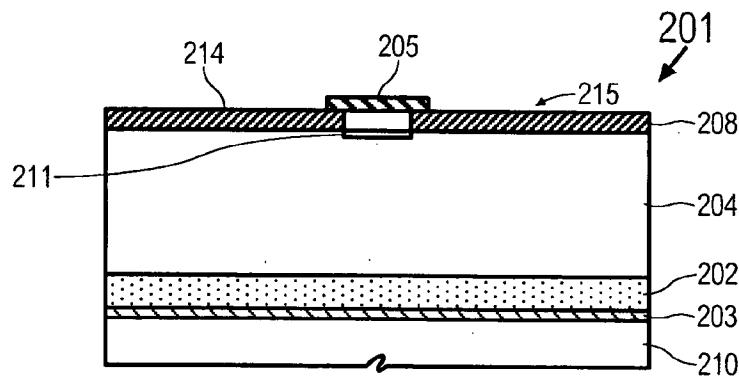


FIGURE 4

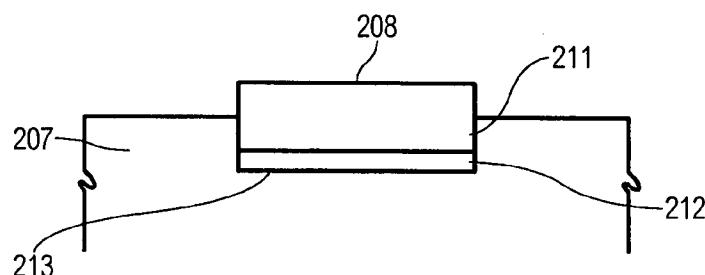


FIGURE 5

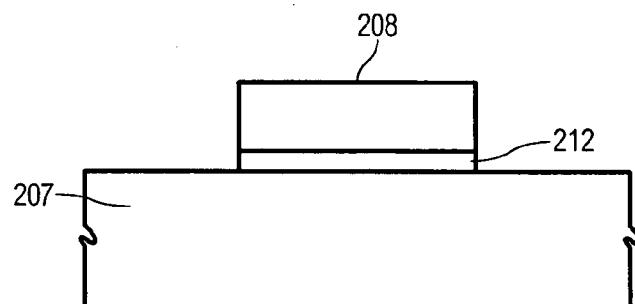
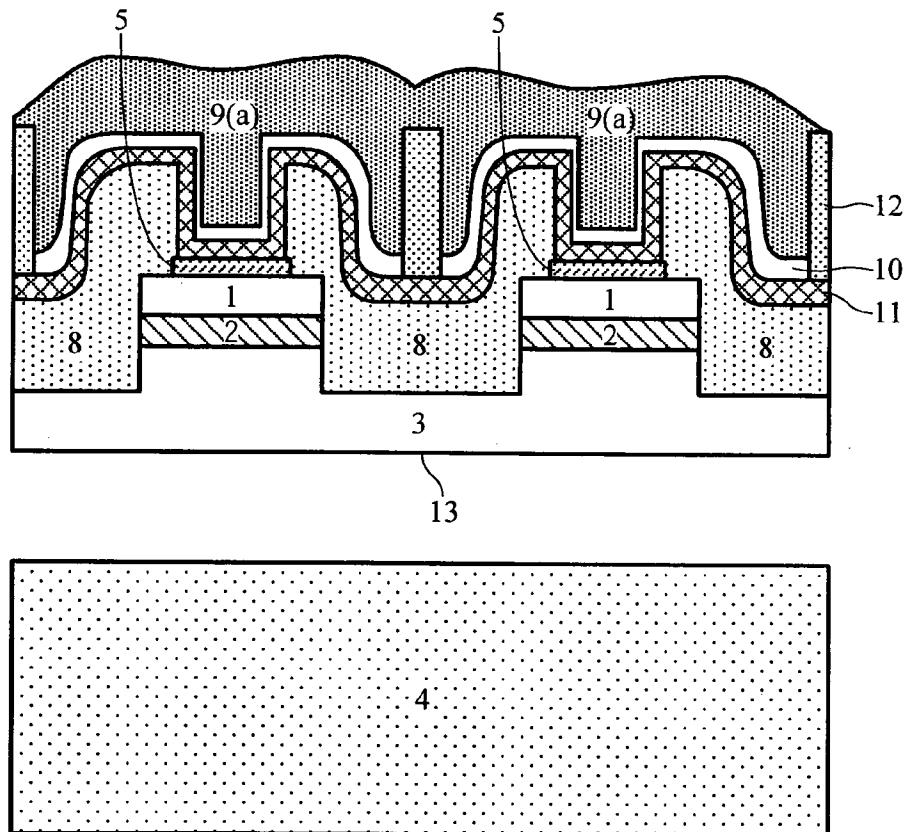
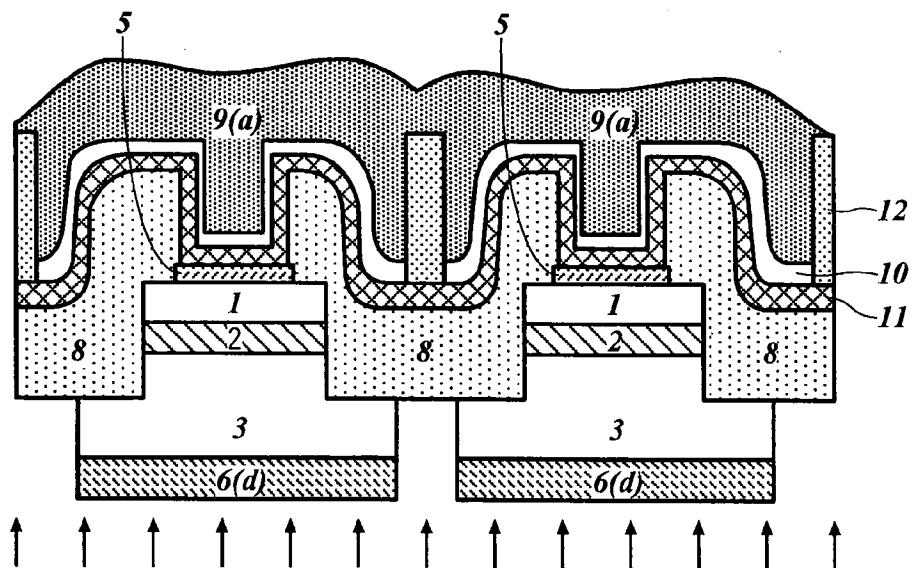


FIGURE 6

3/8

**FIGURE 7****FIGURE 8**

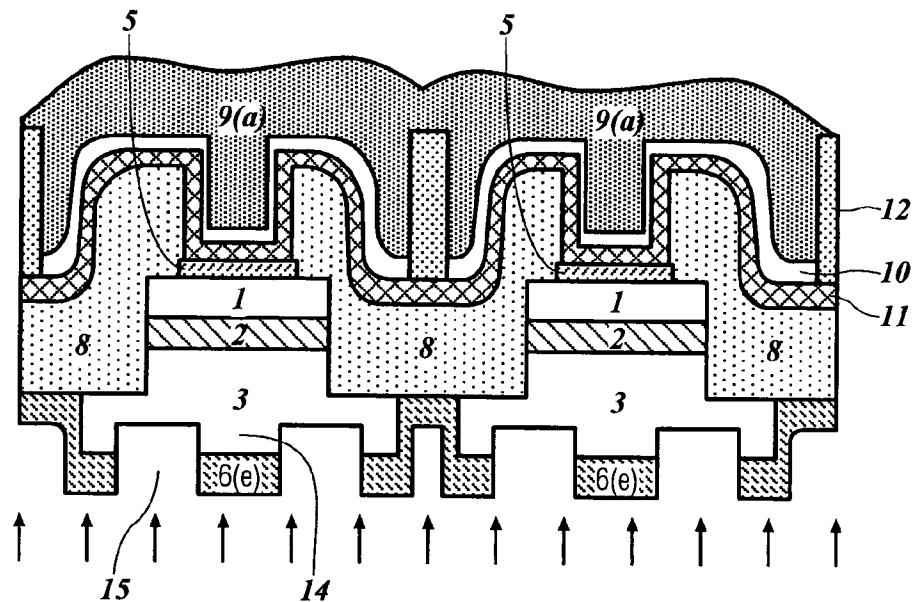


FIGURE 9A

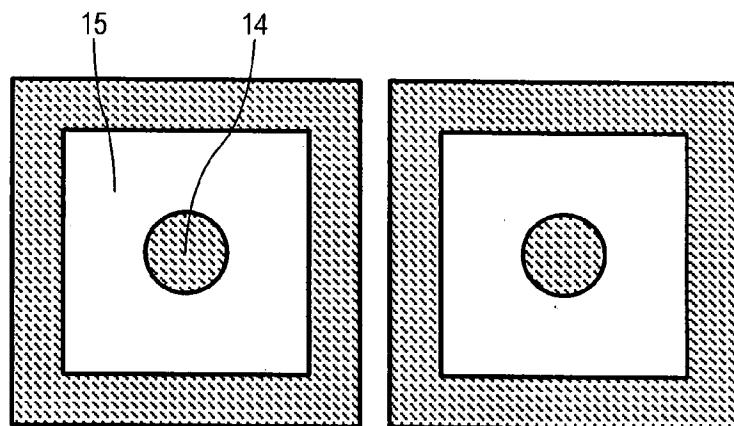


FIGURE 9B

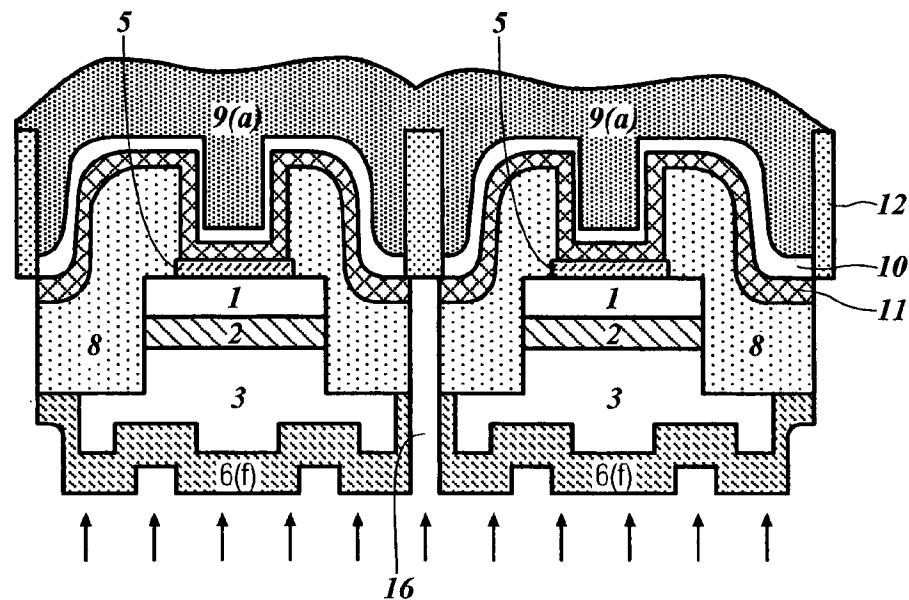


FIGURE 10A

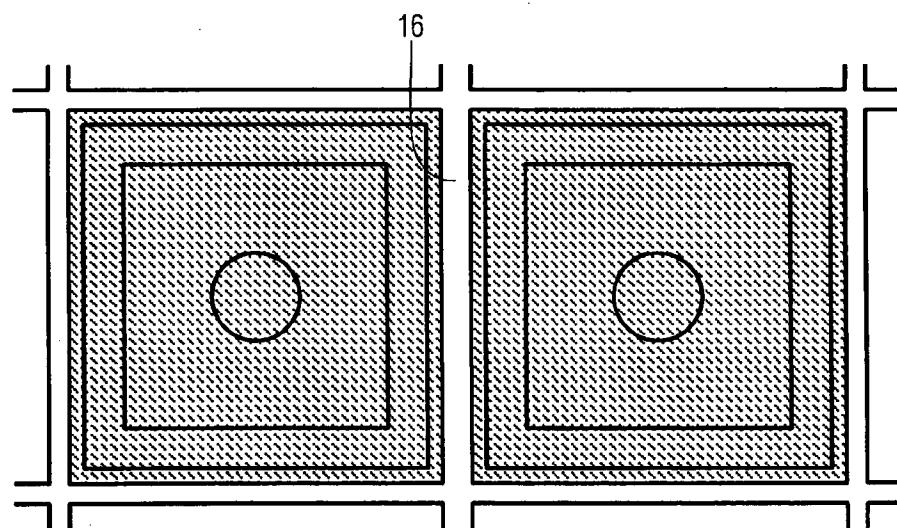


FIGURE 10B

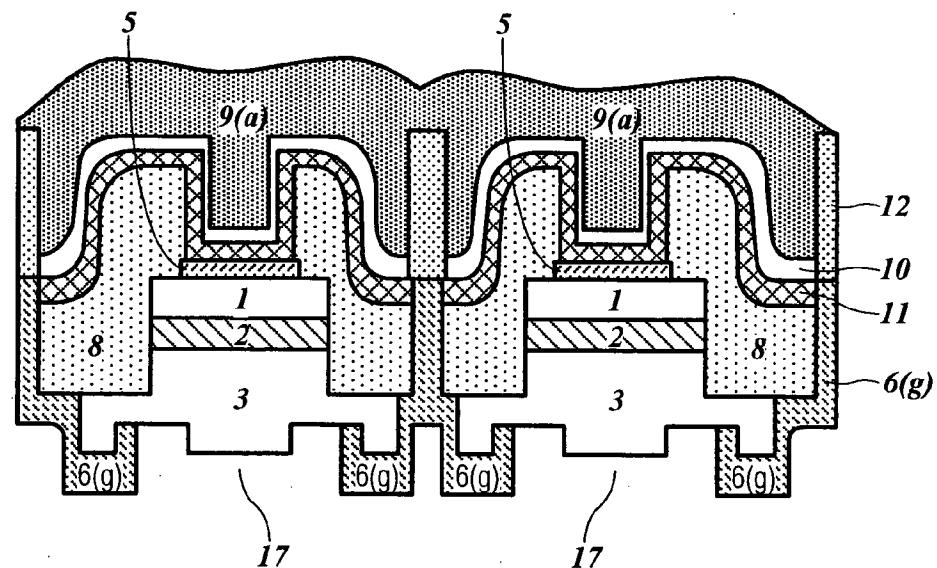


FIGURE 11A

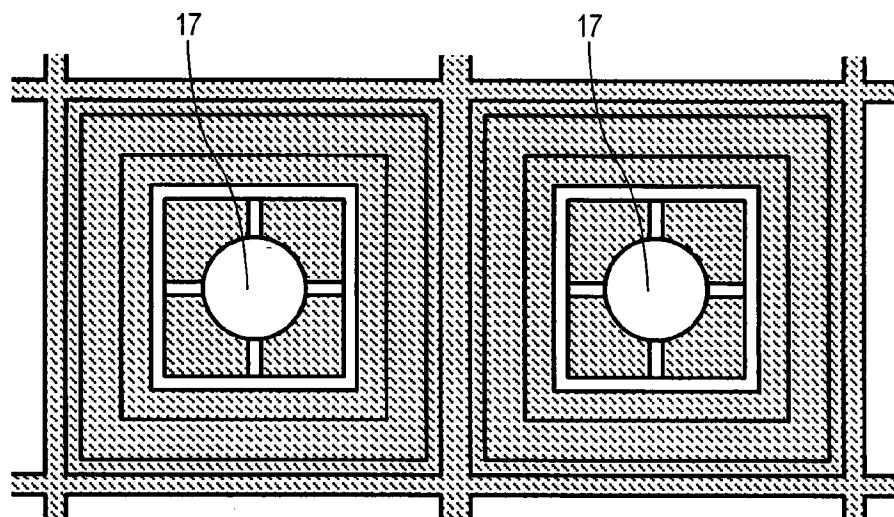


FIGURE 11B

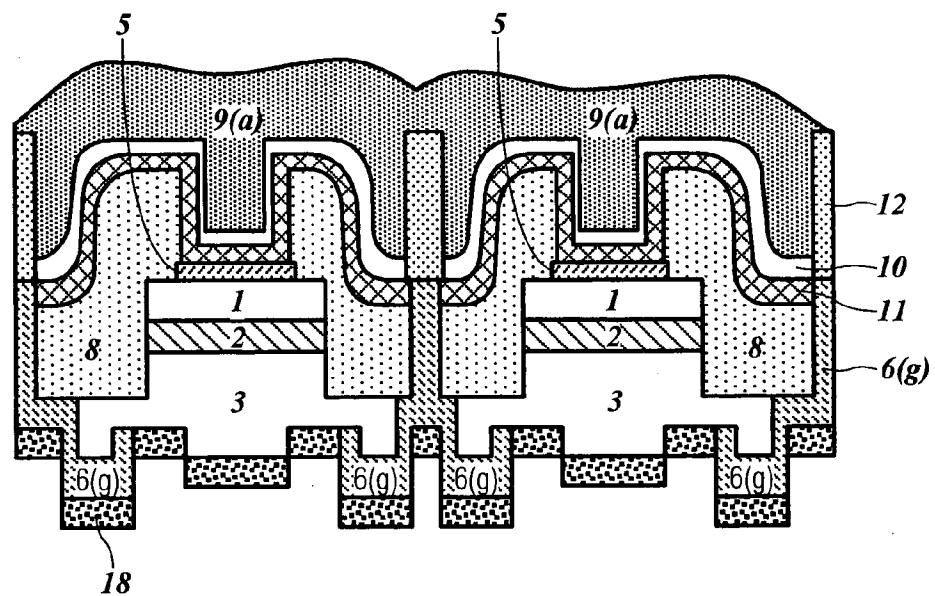


FIGURE 12

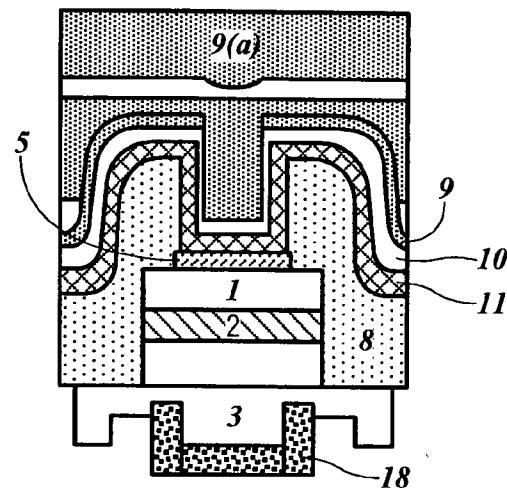


FIGURE 13A

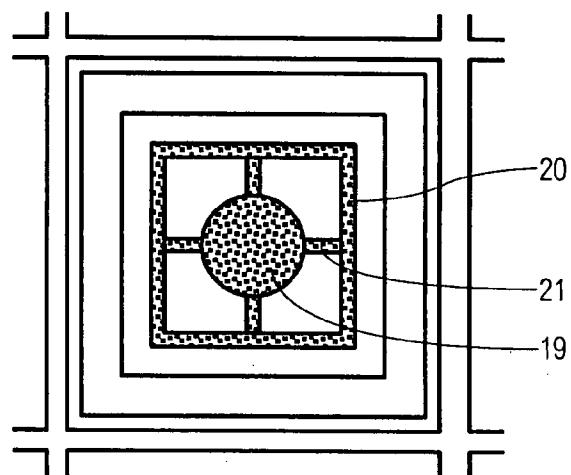


FIGURE 13B

INTERNATIONAL SEARCH REPORT

International application No.

PCT/SG2007/000288

A. CLASSIFICATION OF SUBJECT MATTER

Int. Cl.

H01L 33/00 (2006.01) H01L 23/482 (2006.01)

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
 DWPI limit H01L/IC, (LED or light emitting diode or laser diode or photoelectric diode), (conduct, terminal, electrode, metal, contact, pad), (grid or array or pattern), (layer or film or top), (current or light), (spread or diffuse or distribute or dissipate), (bond or connect or link), pad , spoke or joint

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	JP 2001237461 A (TOSHIBA CORP) 31 August 2001 Paragraphs 0010, 0013, 0022, 0024, 0033, Figs. 1-3	1-4, 7-10
X	US 2005/0082555 A1 (CHIEN ET AL.) 21 April 2005 Paragraphs 0031, 0034, 0043, Figs. 2A-2E	1-4, 7-10
X	US 6307218 B1 (STEIGERWALD ET AL.) 23 October 2001 Column5, lines 22-30, column 9, lines 45-67, Figs. 21C, 22B	1-4, 7-10

 Further documents are listed in the continuation of Box C See patent family annex

* Special categories of cited documents:		
"A" document defining the general state of the art which is not considered to be of particular relevance	"T"	later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"E" earlier application or patent but published on or after the international filing date	"X"	document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"Y"	document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O" document referring to an oral disclosure, use, exhibition or other means	"&"	document member of the same patent family
"P" document published prior to the international filing date but later than the priority date claimed		

Date of the actual completion of the international search
30 October 2007Date of mailing of the international search report
- 9 NOV 2007Name and mailing address of the ISA/AU
AUSTRALIAN PATENT OFFICE
PO BOX 200, WODEN ACT 2606, AUSTRALIA
E-mail address: pct@ipaaustralia.gov.au
Facsimile No. (02) 6285 3929Authorized officer
JAYATI RAY
AUSTRALIAN PATENT OFFICE
(ISO 9001 Quality Certified Service)
Telephone No : (02) 6283

INTERNATIONAL SEARCH REPORT

International application No.

PCT/SG2007/000288

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 2005/0087884 A1 (STOKES ET AL.) 28 April, 2005 Paragraphs 0022, 0025, 0028-0029, Fig. 1	1, 7
X	US 2005/0093002 A1 (TSAI ET AL.) 5 May 2005 Paragraphs 0021, 0031, Figs. 2a-2b	1-12
X	US 2005/0035354 A1 (LIN ET AL.) 17 February 2005 Paragraphs 0030, 0031, 0037, Figs. 4-5, 8-9	1-4, 7-10
X	US 6420732 B1 (KUNG ET AL.) 16 July 2002 Column 10, lines 53-67, Figs. 5-12	1-4, 7-10
A	US 2003/0111667 A1 (SCHUBERT) 19 June 2003 Whole document	

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/SG2007/000288

This Annex lists the known "A" publication level patent family members relating to the patent documents cited in the above-mentioned international search report. The Australian Patent Office is in no way liable for these particulars which are merely given for the purpose of information.

Patent Document Cited in Search Report			Patent Family Member			
JP	2001237461	NONE				
US	2005082555	US	6958496			
US	6307218	DE	19953160	GB	2343994	JP
US	2005087884	US	7119372			
US	2005093002	US	7012281			
US	2005035354	CN	1670972	US	6958494	
US	6420732	NONE				
US	2003111667	AU	2002360581	CA	2470095	EP
		US	6784462	WO	03052838	1454369

Due to data integration issues this family listing may not include 10 digit Australian applications filed since May 2001.

END OF ANNEX